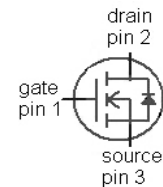


OptiMOS[®] 2 Power-Transistor
Features

- N-channel, normal level
- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC¹⁾ for target application
- Ideal for high-frequency switching and synchronous rectification

Product Summary

V_{DS}	100	V
$R_{DS(on),max}$	64	m Ω
I_D	17	A



Type	IPD64CN10N G	IPU64CN10N G
Package	PG-TO252-3	PG-TO251-3
Marking	64CN10N	64CN10N

Maximum ratings, at $T_j=25$ °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	$T_C=25$ °C	17	A
		$T_C=100$ °C	13	
Pulsed drain current ²⁾	$I_{D,pulse}$	$T_C=25$ °C	68	
Avalanche energy, single pulse	E_{AS}	$I_D=17$ A, $R_{GS}=25$ Ω	34	mJ
Reverse diode dv/dt	dv/dt	$I_D=17$ A, $V_{DS}=80$ V, $di/dt=100$ A/ μ s, $T_{j,max}=175$ °C	6	kV/ μ s
Gate source voltage ³⁾	V_{GS}		± 20	V
Power dissipation	P_{tot}	$T_C=25$ °C	44	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 175	°C
IEC climatic category; DIN IEC 68-1			55/175/56	

¹⁾J-STD20 and JESD22

²⁾ see figure 3

³⁾ $T_{j,max}=150$ °C and duty cycle $D=0.01$ for $V_{GS}<-5$ V

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics						
Thermal resistance, junction - case	R_{thJC}		-	-	3.4	K/W
Thermal resistance, junction - ambient (TO252)		minimal footprint	-	-	75	
		6 cm ² cooling area ⁴⁾	-	-	50	

Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}, I_D=1\text{ mA}$	100	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=20\text{ }\mu\text{A}$	2	3	4	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=80\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ °C}$	-	0.1	1	μA
		$V_{DS}=80\text{ V}, V_{GS}=0\text{ V}, T_j=125\text{ °C}$	-	10	100	
Gate-source leakage current	I_{GSS}	$V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$	-	1	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}, I_D=17\text{ A}$	-	45	64	m Ω
Gate resistance	R_G		-	1.6	-	Ω
Transconductance	g_{fs}	$ V_{DS} >2 I_D R_{DS(on)max}, I_D=17\text{ A}$	8	15	-	S

⁴⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic characteristics						
Input capacitance	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=50\text{ V},$ $f=1\text{ MHz}$	-	428	569	pF
Output capacitance	C_{oss}		-	132	176	
Reverse transfer capacitance	C_{rss}		-	6	10	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=50\text{ V}, V_{GS}=10\text{ V},$ $I_D=17\text{ A}, R_G=1.6\ \Omega$	-	7	11	ns
Rise time	t_r		-	3	4	
Turn-off delay time	$t_{d(off)}$		-	9	14	
Fall time	t_f		-	2	4	

Gate Charge Characteristics⁵⁾

Gate to source charge	Q_{gs}	$V_{DD}=50\text{ V}, I_D=17\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	3	4	nC
Gate to drain charge	Q_{gd}		-	2	3	
Switching charge	Q_{sw}		-	3	4	
Gate charge total	Q_g		-	6	9	
Gate plateau voltage	$V_{plateau}$		-	6.3	-	V
Output charge	Q_{oss}	$V_{DD}=50\text{ V}, V_{GS}=0\text{ V}$	-	13	18	nC

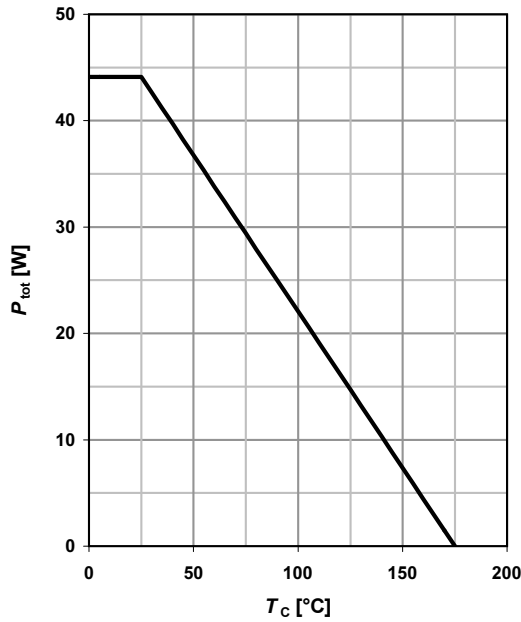
Reverse Diode

Diode continuous forward current	I_S	$T_C=25\text{ }^\circ\text{C}$	-	-	17	A
Diode pulse current	$I_{S,pulse}$		-	-	68	
Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=17\text{ A},$ $T_j=25\text{ }^\circ\text{C}$	-	1	1.2	V
Reverse recovery time	t_{rr}	$V_R=50\text{ V}, I_F=I_S,$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	70	-	ns
Reverse recovery charge	Q_{rr}		-	120	-	nC

⁵⁾ See figure 16 for gate charge parameter definition

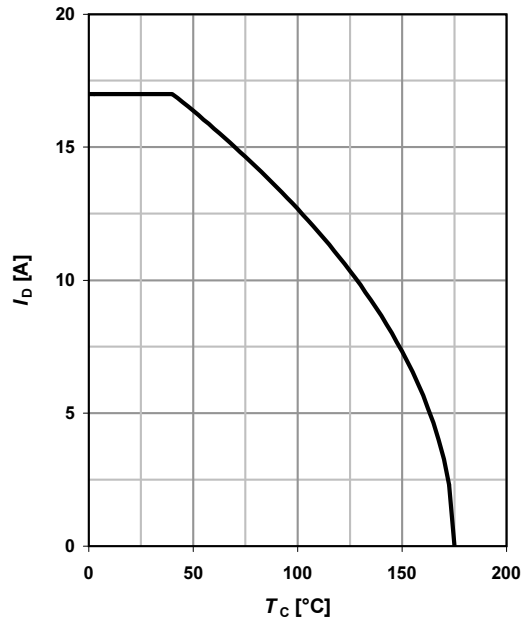
1 Power dissipation

$$P_{tot} = f(T_C)$$



2 Drain current

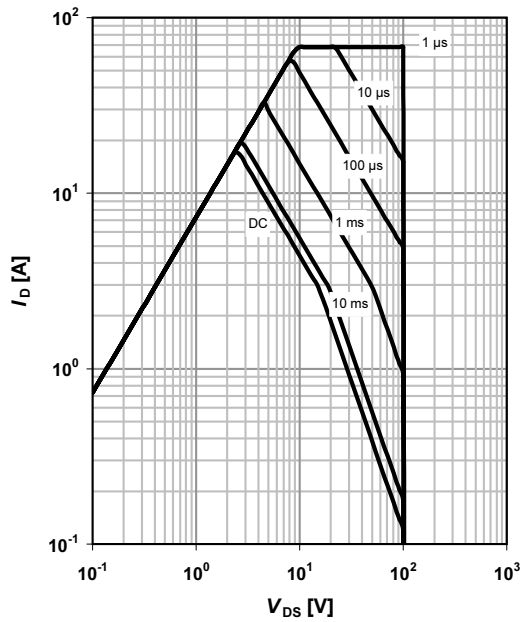
$$I_D = f(T_C); V_{GS} \geq 10 \text{ V}$$



3 Safe operating area

$$I_D = f(V_{DS}); T_C = 25 \text{ °C}; D = 0$$

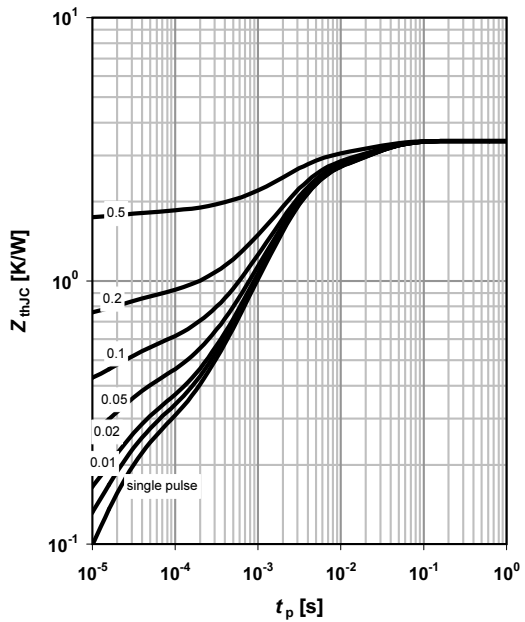
parameter: t_p



4 Max. transient thermal impedance

$$Z_{thJC} = f(t_p)$$

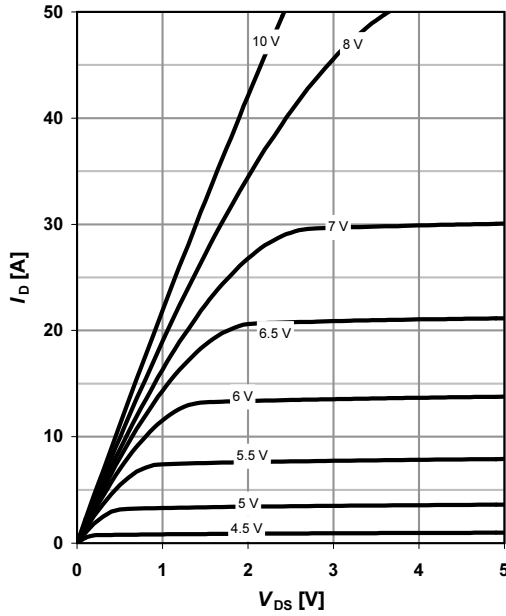
parameter: $D = t_p/T$



5 Typ. output characteristics

$I_D = f(V_{DS}); T_j = 25\text{ °C}$

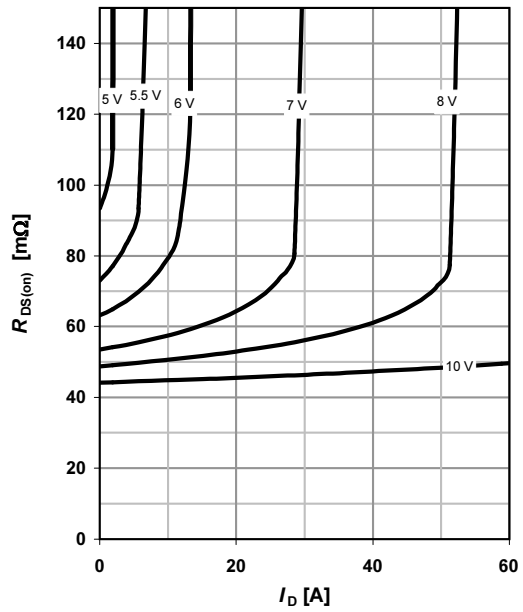
parameter: V_{GS}



6 Typ. drain-source on resistance

$R_{DS(on)} = f(I_D); T_j = 25\text{ °C}$

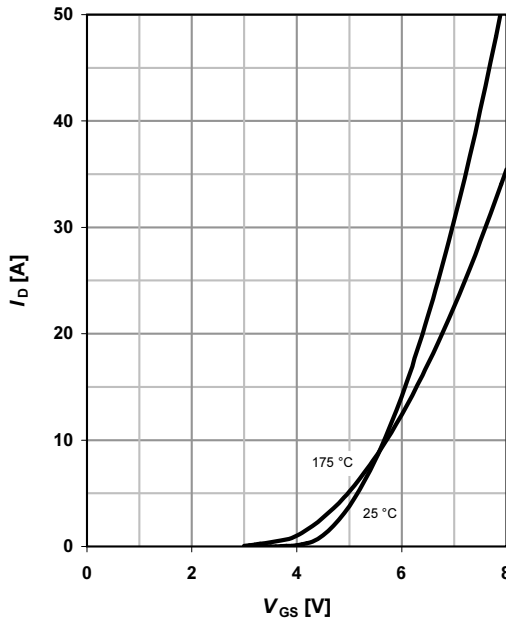
parameter: V_{GS}



7 Typ. transfer characteristics

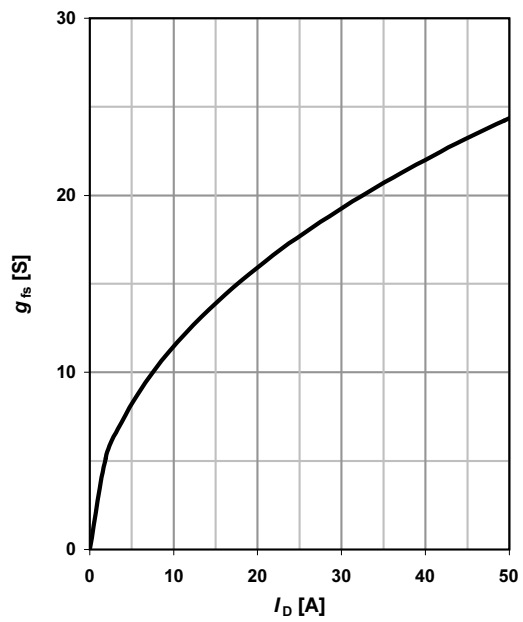
$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

parameter: T_j



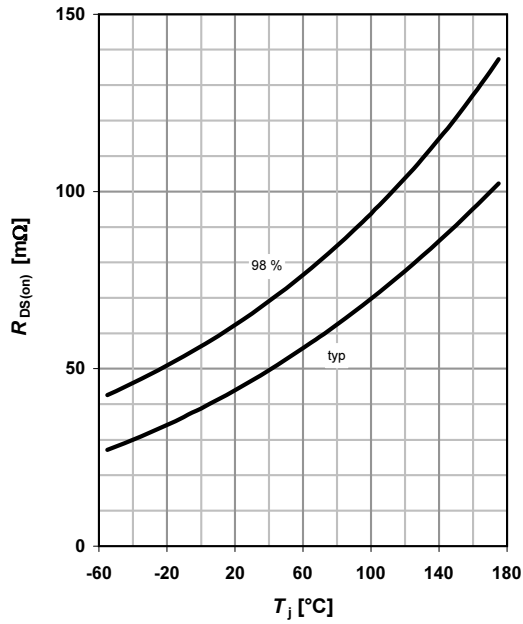
8 Typ. forward transconductance

$g_{fs} = f(I_D); T_j = 25\text{ °C}$



9 Drain-source on-state resistance

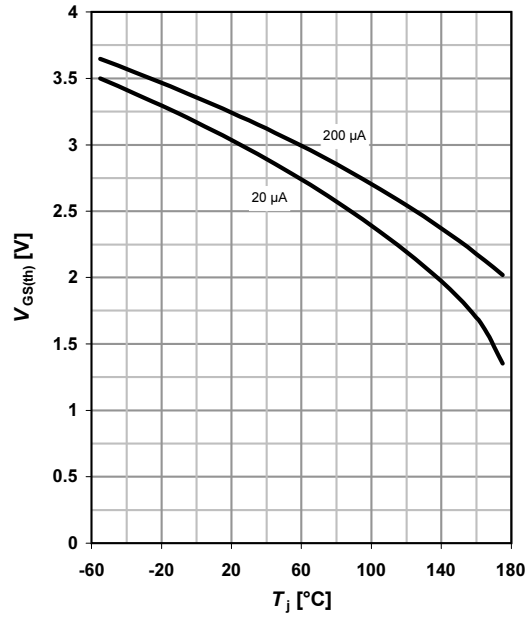
$$R_{DS(on)} = f(T_j); I_D = 17 \text{ A}; V_{GS} = 10 \text{ V}$$



10 Typ. gate threshold voltage

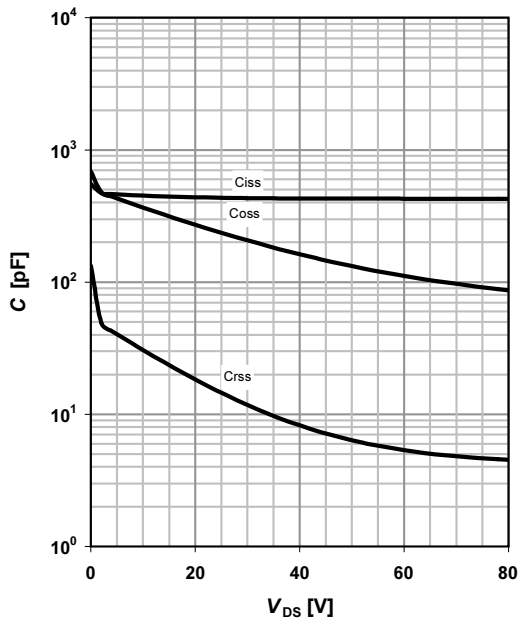
$$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$$

parameter: I_D



11 Typ. capacitances

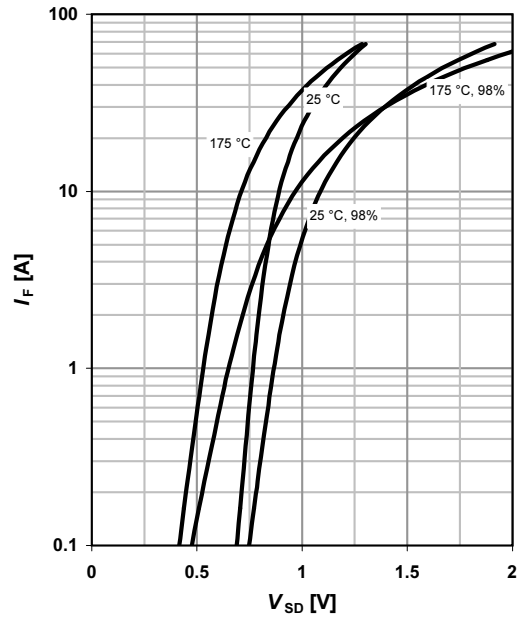
$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$



12 Forward characteristics of reverse diode

$$I_F = f(V_{SD})$$

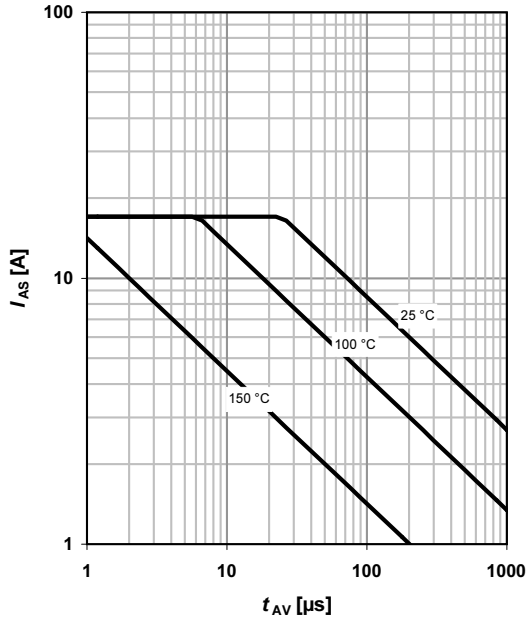
parameter: T_j



13 Avalanche characteristics

$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$

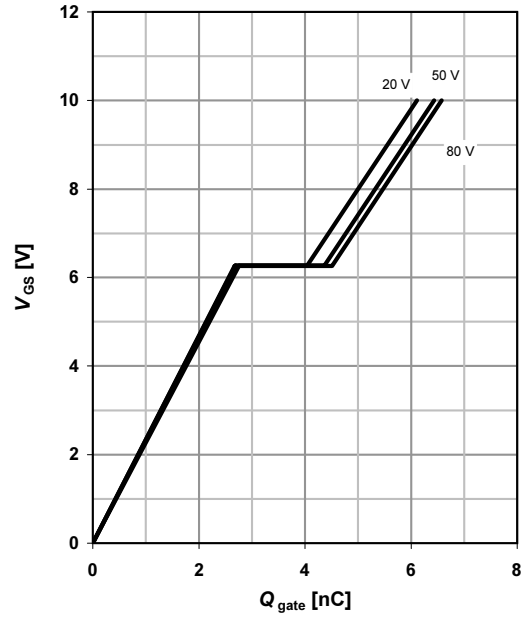
parameter: $T_{j(\text{start})}$



14 Typ. gate charge

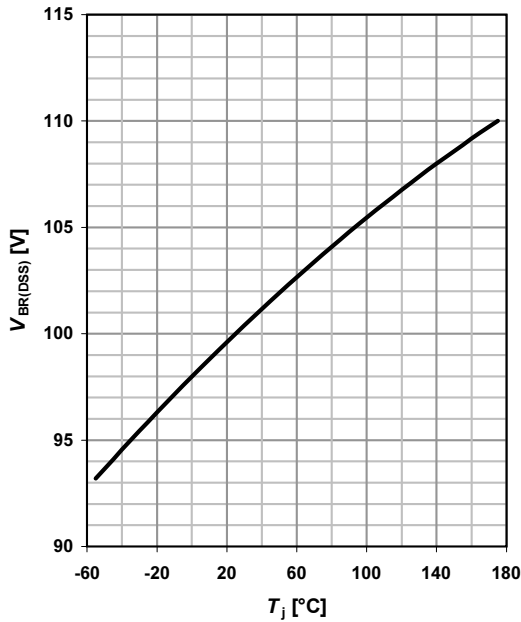
$V_{GS}=f(Q_{\text{gate}}); I_D=17 \text{ A pulsed}$

parameter: V_{DD}

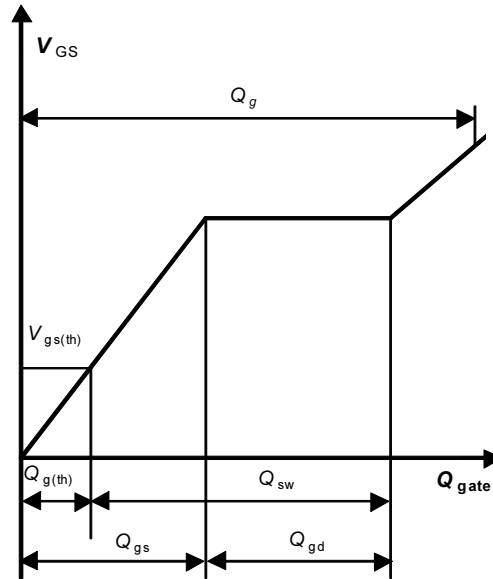


15 Drain-source breakdown voltage

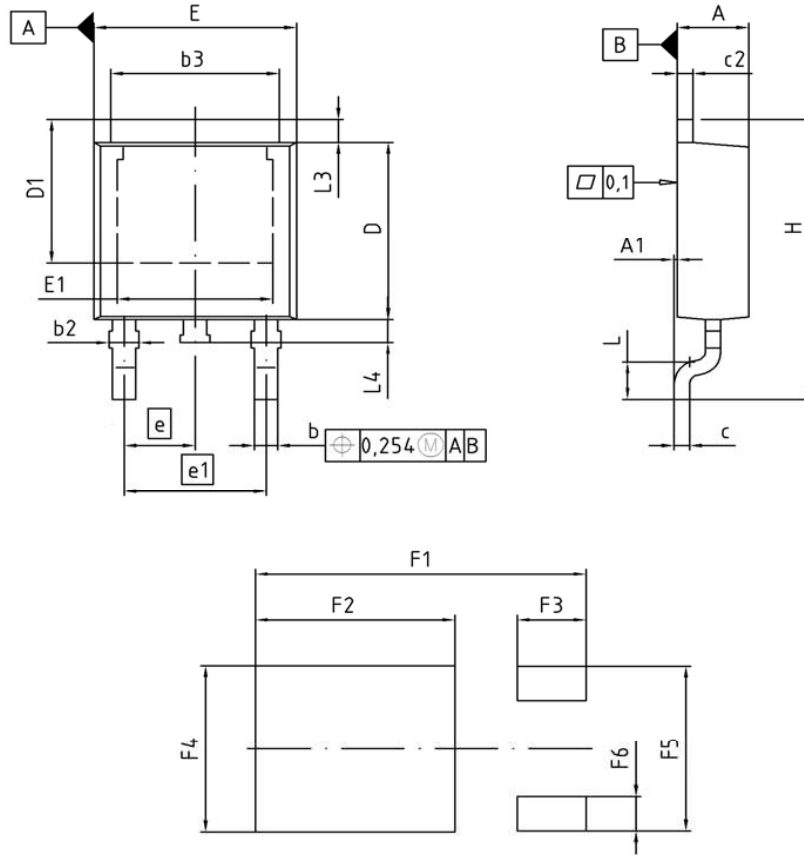
$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$



16 Gate charge waveforms



PG-TO252-3: Outline



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.16	2.41	0.085	0.095
A1	0.00	0.15	0.000	0.006
b	0.64	0.89	0.025	0.035
b2	0.65	1.15	0.026	0.045
b3	5.00	5.50	0.197	0.217
c	0.46	0.60	0.018	0.024
c2	0.46	0.98	0.018	0.039
D	5.97	6.22	0.235	0.245
D1	5.02	5.84	0.198	0.230
E	6.40	6.73	0.252	0.265
E1	4.70	5.21	0.185	0.205
e	2.29		0.090	
e1	4.57		0.180	
N	3		3	
H	9.40	10.48	0.370	0.413
L	1.18	1.70	0.046	0.067
L3	0.90	1.25	0.035	0.049
L4	0.51	1.00	0.020	0.039
F1	10.50	10.70	0.413	0.421
F2	6.30	6.50	0.248	0.256
F3	2.10	2.30	0.083	0.091
F4	5.70	5.90	0.224	0.232
F5	5.66	5.86	0.223	0.231
F6	1.10	1.30	0.043	0.051

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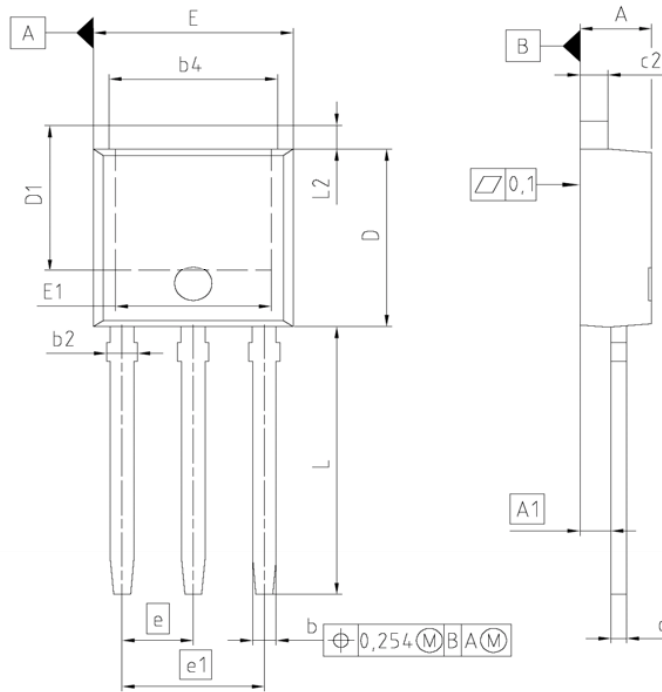
SCALE

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03

PG-TO251-3: Outline



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.159	2.413	0.085	0.095
A1	0.900	1.118	0.035	0.044
b	0.650	0.850	0.026	0.033
b2	0.650	1.150	0.026	0.045
b4	5.004	5.500	0.197	0.217
c	0.457	0.580	0.018	0.023
c2	0.737	0.980	0.029	0.039
D	5.969	6.223	0.235	0.245
D1	5.100	6.121	0.201	0.241
E	6.400	6.731	0.252	0.265
E1	4.850	5.207	0.191	0.205
e	2.286		0.090	
e1	4.572		0.180	
N	3		3	
L	8.900	9.525	0.350	0.375
L1	0.900	1.143	0.035	0.045

REFERENCE
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SCALE 0 2.0 4mm

EUROPEAN PROJECTION

ISSUE DATE
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